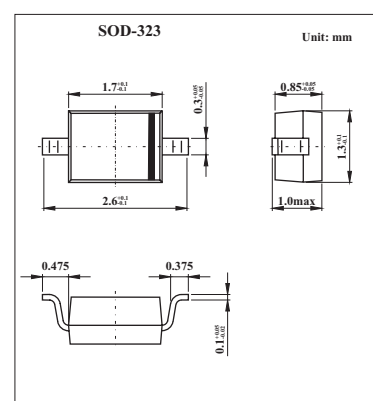


## Silicon Epitaxial Planar Pin Diode

## HVU133

## ■ Features

- Low capacitance. (C=1.0pF max)
- Low forward resistance. ( $r_f=0.7\ \Omega$  max)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	30	V
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	$V_R$	$I_R = 1\ \mu\text{A}$	30			V
Reverse current	$I_R$	$V_R = 25\ \text{V}$			100	nA
Forward voltage	$V_F$	$I_F = 2\ \text{mA}$			0.85	V
Capacitance	C1	$V_R = 1\ \text{V}, f = 1\ \text{MHz}$			1.0	pF
	C6	$V_R = 6\ \text{V}, f = 1\ \text{MHz}$			0.9	
Forward resistance	$r_f$	$I_F = 2\ \text{mA}, f = 100\ \text{MHz}$		0.55	0.7	$\Omega$

## ■ Marking

Marking	P3
---------	----